# The RF Line **UHF Power Transistor**

... designed primarily for large-signal output and driver amplifier stages to 1.0 GHz.

- Designed for Class A Linear Power Amplifiers
- Specified 25 Volt, 900 MHz Characteristics: Output Power - 6.0 Watts Power Gain - 6.5 dB Min, Class AB
- Gold Metallization for Improved Reliability

CASE 244-04, STYLE 1 (.280 SOE)

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	VCEO	30	Vdc
Collector-Base Voltage	VCBO	60	Vdc
Emitter–Base Voltage	VEBO	4.0	Vdc
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	PD	50 0.286	Watts W/°C
Operating Junction Temperature	ТJ	200	°C
Storage Temperature Range	T <sub>stg</sub>	-65 to +150	°C

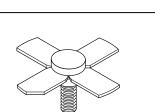
### THERMAL CHARACTERISTICS

Characteristic	Symbol	Мах	Unit
Thermal Resistance, Junction to Case (T <sub>C</sub> = 70°C)	R <sub>θ</sub> JC	3.5	°C/W

## **ELECTRICAL CHARACTERISTICS**

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage ( $I_C = 20 \text{ mA}, I_B = 0$ )	V(BR)CEO	30	-	-	Vdc
Collector–Emitter Breakdown Voltage $(I_{C} = 20 \text{ mA}, V_{BE} = 0)$	V <sub>(BR)</sub> CES	60	-	-	Vdc
Collector–Base Breakdown Voltage ( $I_C = 20 \text{ mA}, I_E = 0$ )	V <sub>(BR)</sub> CBO	60	-	-	Vdc
Emitter–Base Breakdown Voltage $(I_E = 5.0 \text{ mA}, I_C = 0)$	V <sub>(BR)EBO</sub>	4.0	-	_	Vdc
Collector Cutoff Current ( $V_{CB} = 25 \text{ V}, I_E = 0$ )	ICBO	_	-	3.0	mAdc
ON CHARACTERISTICS					
DC Current Gain (I <sub>C</sub> = 1.0 mA, $V_{CE}$ = 5.0 V)	hFE	20	-	80	—
DYNAMIC CHARACTERISTICS					
Output Capacitance ( $V_{CB}$ = 28 V, I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>ob</sub>	_	-	19.5	pF
FUNCTIONAL TESTS					-
Common Emitter Amplifier Power Gain ( $V_{CE} = 25 \text{ V}, \text{ P}_{Out} = 6.0 \text{ W}, \text{ f} = 900 \text{ MHz}, \text{ I}_{C} = 0.85 \text{ A}$ )	GPE	6.5	7.5	-	dB
Load Mismatch (V <sub>CE</sub> = 25 V, P <sub>OUt</sub> = 6.0 W, f = 900 MHz, Load VSWR = $\infty$ :1, All Phase Angles)	Ψ	No Degradation in Output Power			





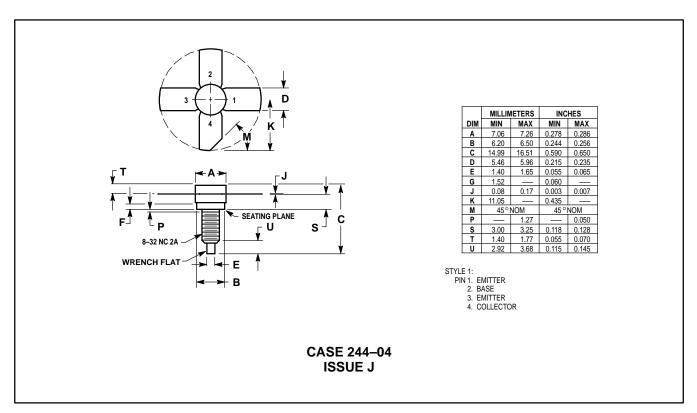
**MRF1032** 

6.0 W, TO 1.0 GHz LINEAR

UHF POWER TRANSISTOR NPN SILICON



#### PACKAGE DIMENSIONS



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